

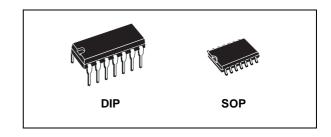


EXPANDABLE 4-WIDE 2-INPUT AND-OR INVERTER GATE

- MEDIUM-SPEED OPERATION t_{PHL} = 90ns, t_{PLH} = 140ns (Typ.) at 10V
- INHIBIT AND ENABLE INPUTS
- QUIESCENT CURRENT SPECIFIED UP TO 20V
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- 5V, 10V AND 15V PARAMETRIC RATINGS
- INPUT LEAKAGE CURRENT I_I = 100nA (MAX) AT V_{DD} = 18V T_A = 25°C
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC JESD13B "STANDARD SPECIFICATIONS FOR DESCRIPTION OF B SERIES CMOS DEVICES"



HCF4086B is a monolithic integrated circuit fabricated in Metal Oxide Semiconductor technology available in DIP and SOP packages.

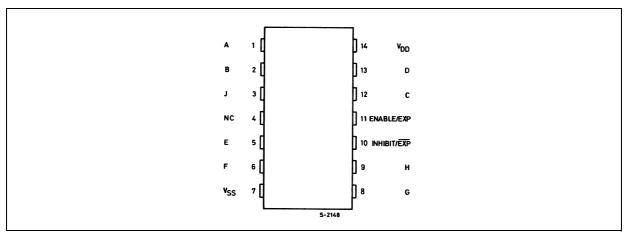


ORDER CODES

PACKAGE	TUBE	T&R
DIP	HCF4086BEY	
SOP	HCF4086BM1	HCF4086M013TR

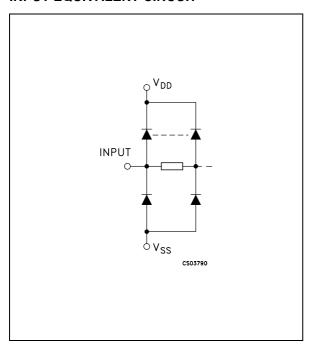
HCF4086B contains one 4-wide 2-input AND-OR INVERT gates with an INHIBIT EXP input and an ENABLE/EXP input. INHIBIT/EXP is tied to V_{SS} and ENABLE/EXP to V_{DD} . For a 4 wide A-O-I function.

PIN CONNECTION



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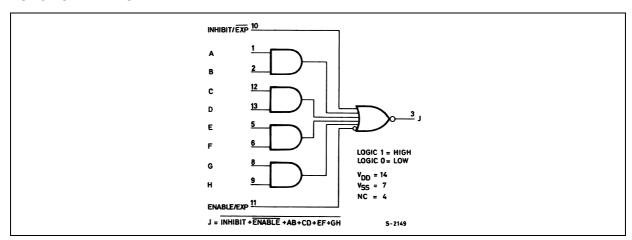
INPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1, 2, 12, 13, 5, 6, 8, 9	A to H	Data Inputs
3	J	Output
10	INHIBIT/EXP	Inhibit Input
10	ENABLE/ EXP	Enable Input
4	NC	Not Connected
7	V _{SS}	Negative Supply Voltage
14	V_{DD}	Positive Supply Voltage

FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage	-0.5 to +22	V
V _I	DC Input Voltage	-0.5 to V _{DD} + 0.5	V
I _I	DC Input Current	± 10	mA
P _D	Power Dissipation per Package	200	mW
	Power Dissipation per Output Transistor	100	mW
T _{op}	Operating Temperature	-55 to +125	°C
T _{stg}	Storage Temperature	-65 to +150	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage	3 to 20	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature	-55 to 125	°C

DC SPECIFICATIONS

			Test Con	dition		Value							Unit
Symbol Parameter	V _I	v _o	ll _o l '	V _{DD}	T _A = 25°C		-40 to 85°C		-55 to 125°C				
		(V)	(V)	(μA)	(V)	Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
ΙL	Quiescent Current	0/5			5		0.02	1		30		30	
		0/10			10		0.02	2		60		60	^
		0/15			15		0.02	4		120		120	μΑ
		0/20			20		0.04	20		600		600	
V _{OH}	High Level Output	0/5		<1	5	4.95			4.95		4.95		
	Voltage	0/10		<1	10	9.95			9.95		9.95		V
		0/15		<1	15	14.95			14.95		14.95		
V _{OL}	Low Level Output	5/0		<1	5		0.05			0.05		0.05	
	Voltage	10/0		<1	10		0.05			0.05		0.05	V
		15/0		<1	15		0.05			0.05		0.05	
V _{IH}	High Level Input		0.5/4.5	<1	5	3.5			3.5		3.5		
	Voltage		1/9	<1	10	7			7		7		V
			1.5/13.5	<1	15	11			11		11		
V _{IL}	Low Level Input		4.5/0.5	<1	5			1.5		1.5		1.5	
	Voltage		9/1	<1	10			3		3		3	V
			13.5/1.5	<1	15			4		4		4	
I _{OH}	Output Drive	0/5	2.5	<1	5	-1.36	-3.2		-1.15		-1.1		
	Current	0/5	4.6	<1	5	-0.44	-1		-0.36		-0.36		A
		0/10	9.5	<1	10	-1.1	-2.6		-0.9		-0.9		mA
		0/15	13.5	<1	15	-3.0	-6.8		-2.4		-2.4		
I _{OL} Output S	Output Sink	0/5	0.4	<1	5	0.44	1		0.36		0.36		
	Current	0/10	0.5	<1	10	1.1	2.6		0.9		0.9		mΑ
		0/15	1.5	<1	15	3.0	6.8		2.4		2.4		
II	Input Leakage Current	0/18	Any In	put	18		±10 ⁻⁵	±0.1		±1		±1	μΑ
C _I	Input Capacitance		Any In	put			5	7.5					pF
	l	·			-> / ->	·	·	L	L	·	L		

The Noise Margin for both "1" and "0" level is: 1V min. with V_{DD} =5V, 2V min. with V_{DD} =10V, 2.5V min. with V_{DD} =15V

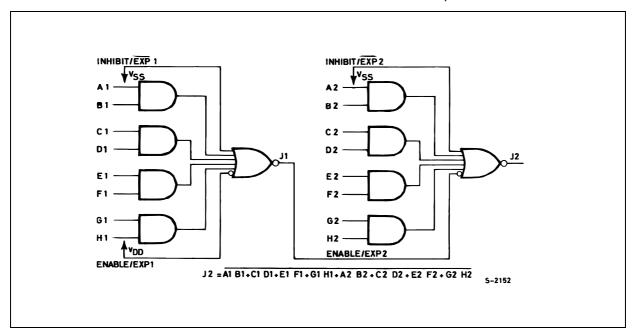
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 $\textbf{DYNAMIC ELECTRICAL CHARACTERISTICS} \; (\textbf{T}_{amb} = 25^{\circ} \textbf{C}, \;\; \textbf{C}_{L} = 50 \text{pF}, \; \textbf{R}_{L} = 200 \text{K}\Omega, \;\; \textbf{t}_{r} = \textbf{t}_{f} = 20 \; \text{ns})$

	_		,	Value (*)			
Symbol	Parameter	V _{DD} (V)		Min.	Тур.	Max.	
t _{PHL}	Propagation Delay Time	5			225	450	
	(DATA)	10			90	180	ns
		15			60	120	
t _{PLH}	Propagation Delay Time	5			310	620	
	(DATA)	10			125	250	ns
		15			90	180	
t _{PHL}	Propagation Delay Time	5			150	300	
	(INHIBIT)	10			60	120	ns
		15			40	80	
t _{PLH}	Propagation Delay Time	5			250	500	
	(INHIBIT)	10			100	200	ns
		15			70	140	
t _{TLH} t _{THL}	t _{TLH} t _{THL} Transition Time	5			100	200	
		10			50	100	ns
		15			40	80	

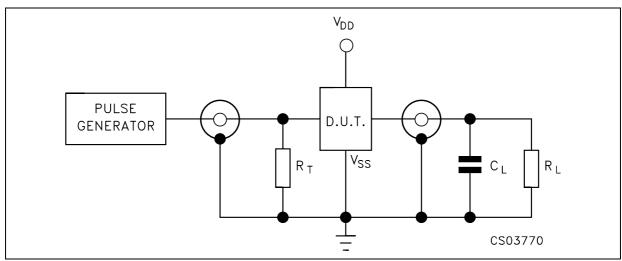
^(*) Typical temperature coefficient for all $\rm V_{DD}$ value is 0.3 %/°C.

TYPICAL APPLICATION: Two HCF4086B Connected as an 8 wide 2 input A-O-I Gate



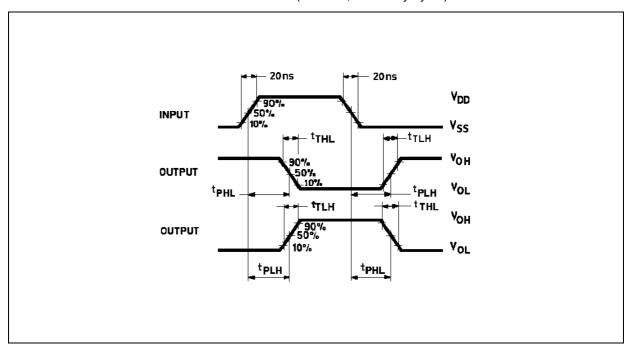
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TEST CIRCUIT



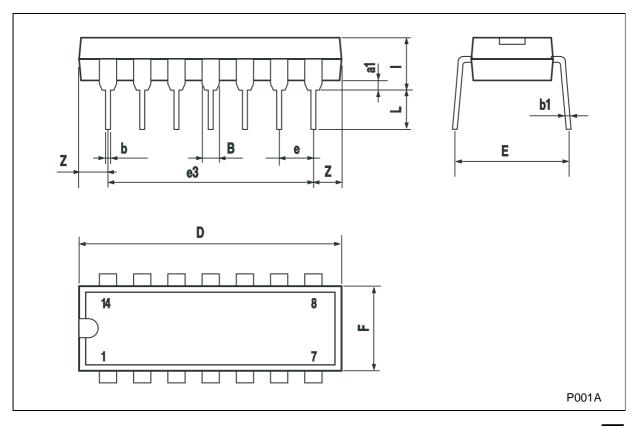
 C_L = 50pF or equivalent (includes jig and probe capacitance) R_L = 200 $K\Omega$ R_T = Z_{OUT} of pulse generator (typically 50 Ω)

WAVEFORM: PROPAGATION DELAY TIMES (f=1MHz; 50% duty cycle)



Plastic DIP-14 MECHANICAL DATA

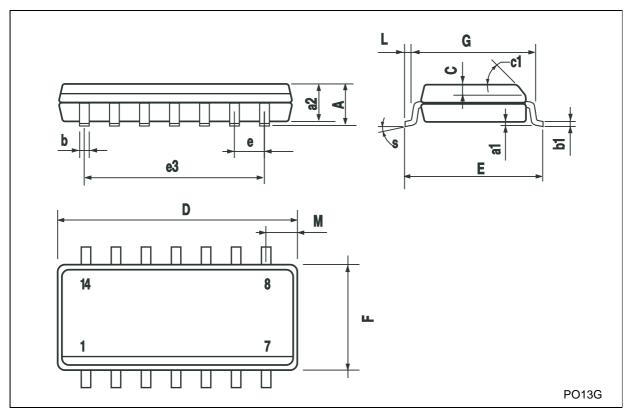
DIM		mm.		inch				
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.		
a1	0.51			0.020				
В	1.39		1.65	0.055		0.065		
b		0.5			0.020			
b1		0.25			0.010			
D			20			0.787		
E		8.5			0.335			
е		2.54			0.100			
e3		15.24			0.600			
F			7.1			0.280		
I			5.1			0.201		
L		3.3			0.130			
Z	1.27		2.54	0.050		0.100		



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SO-14 MECHANICAL DATA

DIM		mm.		inch				
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.		
А			1.75			0.068		
a1	0.1		0.2	0.003		0.007		
a2			1.65			0.064		
b	0.35		0.46	0.013		0.018		
b1	0.19		0.25	0.007		0.010		
С		0.5			0.019			
c1			45°	(typ.)				
D	8.55		8.75	0.336		0.344		
Е	5.8		6.2	0.228		0.244		
е		1.27			0.050			
e3		7.62			0.300			
F	3.8		4.0	0.149		0.157		
G	4.6		5.3	0.181		0.208		
L	0.5		1.27	0.019		0.050		
М			0.68			0.026		
S			8° (1	max.)		•		



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